



Integrated Device Technology, Inc.

32K x 18 16K x 18 CEMOS™ PARALLEL IN-OUT FIFO MODULE

IDT7MP2009
IDT7MP2010

FEATURES:

- First-In/First-Out memory module
- 32K x 18 organization (IDT7MP2009)
- 16K x 18 organization (IDT7MP2010)
- High speed: 15ns (max.) access time
- Separate upper and lower 9-bit XI and XO
- Asynchronous and simultaneous read and write
- Fully expandable by both word depth and/or bit width
- MASTER/SLAVE multiprocessing applications
- Bidirectional and rate buffer applications
- Empty and Full warning-flags
- High-performance CEMOS™ technology
- Single 5V (±10%) power supply

DESCRIPTION:

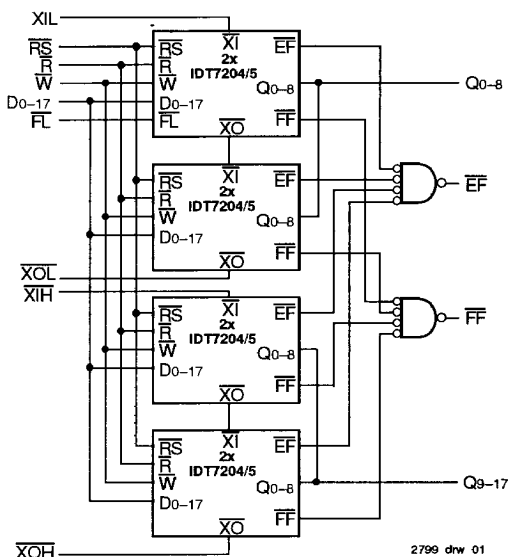
IDT7MP2009/7MP2010 are FIFO memory modules constructed on multi-layered epoxy laminate (FR-4) substrate by mounting eight IDT7205 (8K x 9) or IDT7204 (4K x 9) FIFOs

in plastic leaded chip carriers. Extremely high speeds are achieved in this fashion due to the use of IDT7205s and IDT7204s fabricated in IDT's high performance CEMOS technology. These devices utilize an algorithm that loads and empties data on a first-in/first-out basis. The device uses Full and Empty flags to prevent data overflow and underflow and expansion logic to allow for unlimited expansion capability in both word size and depth.

The reads and writes are internally sequential through the use of ring pointers, with no address information required to load and unload data. Data is toggled in and out of the device through the use of the WRITE (W) and READ (R) pins. The devices have a read/write cycle time of 25ns (min.) for commercial temperature ranges.

The devices utilize a 18-bit wide data array to allow for control and parity bits at the user's option. This feature is especially useful in data communications applications where it is necessary to use a parity bit for transmission/reception error checking.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION

GND	1	2	VCC
XIL	3	4	XOL
D(0)	5	6	Q(0)
D(1)	7	8	Q(1)
D(2)	9	10	Q(2)
D(3)	11	12	Q(3)
D(4)	13	14	Q(4)
D(5)	15	16	Q(5)
D(6)	17	18	Q(6)
D(7)	19	20	Q(7)
D(8)	21	22	Q(8)
FL	23	24	RS
W	25	26	GND
VCC	27	28	R
FF	29	30	EF
XIH	31	32	XOH
D(9)	33	34	Q(9)
D(10)	35	36	Q(10)
D(11)	37	38	Q(11)
D(12)	39	40	Q(12)
D(13)	41	42	Q(13)
D(14)	43	44	Q(14)
D(15)	45	46	Q(15)
D(16)	47	48	Q(16)
D(17)	49	50	Q(17)
VCC	51	52	GND

ZIP
TOP VIEW

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COMMERCIAL TEMPERATURE RANGE

APRIL 1992

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DSC-7053/2

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PIN NAMES

\overline{W}	Write
\overline{R}	Read
\overline{RS}	Reset
\overline{FL}	First Load
D0-17	DATAin
Q0-17	DATAout
$\overline{XIH}, \overline{XIL}$	Expansion In (High Bit, Low Bit)
$\overline{XOH}, \overline{XOL}$	Expansion Out (High Bit, Low Bit)
FF	Full Flag
EF	Empty Flag
VCC	Power
GND	Ground

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RECOMMENDED DC
OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Commercial Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V _{IH} ⁽¹⁾	Input High Voltage Commercial	2.0	—	—	V
V _{IL} ⁽¹⁾	Input Low Voltage Commercial	—	—	0.8	V

NOTE:

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1. 1.5V undershoots are allowed for 10ns once per cycle.

CAPACITANCE (T_A = +25°C, f = 1.0 MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	80	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	120	pF

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NOTE:

1. This parameter is guaranteed by design but not tested.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Com'l.	Unit
V _{TERM}	Terminal Voltage with Respect to GND	−0.5 to +7.0	V
T _A	Operating Temperature	0 to +70	°C
T _{BIAS}	Temperature Under Bias	−10 to +85	°C
T _{STG}	Storage Temperature	−55 to +125	°C
I _{OUT}	DC Output Current	50	mA

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NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL CHARACTERISTICS

(VCC = 5.0V ±10%, T_A = 0°C to +70°C)

Symbol	Parameter	IDT7MP2010		IDT7MP2009		Unit
		Min.	Max.	Min.	Max.	
I _{LI} ⁽¹⁾	Input Leakage Current (Any Input)	—	20	—	20	μA
I _{LO} ⁽²⁾	Output Leakage Current	—	80	—	80	μA
V _{OH}	Output Logic "1" Voltage I _{OUT} = −2mA	2.4	—	2.4	—	V
V _{OL}	Output Logic "0" Voltage I _{OUT} = 8mA	—	0.4	—	0.4	V
I _{CC1} ⁽³⁾	Operating Current	—	1280	—	1200	mA
I _{CC2} ⁽³⁾	Average Standby Current ($\overline{R} = \overline{W} = \overline{RS} = \overline{FL/RT} = V_{IH}$)	—	125	—	115	mA
I _{CC3} ⁽³⁾	Power Down Current (All Input = VCC − 0.2V)	—	65	—	65	mA

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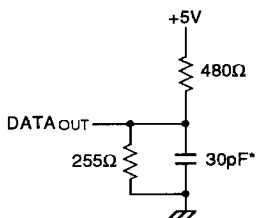
NOTES:

1. Measurements with 0.4 ≤ V_{IN} ≤ V_{OUT}.
2. R ≥ V_{IH}, 0.4 ≤ V_{OUT} ≤ VCC.
3. I_{CC} measurements are made with outputs open.

AC TEST CONDITIONS

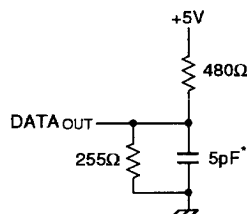
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figure 1 & 2

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Figure 1. Output Load
* Includes scope and jig capacitances.



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Figure 2. Output Load
(for tRLZ, tWLZ, and tRHZ)

AC ELECTRICAL CHARACTERISTICS

(V_{CC} = 5.0V ± 10%, T_A = 0°C to +70°C)

Symbol	Parameter	7MP2009SxxZ, 7MP2010SxxZ										Unit
		-15 ⁽³⁾		-20 ⁽³⁾		-25		-30		-35		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
tRC	Read Cycle Time	25	—	30	—	35	—	40	—	45	—	ns
tA	Access Time	—	15	—	20	—	25	—	30	—	35	ns
tRR	Read Recovery Time	10	—	10	—	10	—	10	—	10	—	ns
tRPW ⁽¹⁾	Read Pulse Width	15	—	20	—	25	—	30	—	35	—	ns
tRLZ ⁽²⁾	Read Pulse Low to Data Bus at Low Z	5	—	5	—	5	—	5	—	5	—	ns
tWLZ ⁽²⁾	Write Pulse High to Data Bus at Low Z	5	—	5	—	5	—	10	—	10	—	ns
tDV	Data Valid from Read Pulse High	5	—	5	—	5	—	5	—	5	—	ns
tRHZ ⁽²⁾	Read Pulse High to Data Bus at High Z	—	15	—	13	—	20	—	20	—	20	ns
tWC	Write Cycle Time	25	—	30	—	35	—	40	—	45	—	ns
tWPW ⁽¹⁾	Write Pulse Width	15	—	20	—	25	—	30	—	35	—	ns
tWR	Write Recovery Time	10	—	10	—	10	—	10	—	10	—	ns
tDS	Data Set-up Time	11	—	15	—	18	—	18	—	20	—	ns
tDH	Data Hold Time	0	—	0	—	0	—	0	—	0	—	ns
tRSC	Reset Cycle Time	25	—	30	—	35	—	40	—	45	—	ns
tRS ⁽¹⁾	Reset Pulse Width	15	—	20	—	25	—	30	—	35	—	ns
tRSR	Reset Recovery Time	10	—	10	—	10	—	10	—	10	—	ns
tEFL	Reset to Empty Flag Low	—	25	—	30	—	35	—	40	—	45	ns
tREF	Read Low to Empty Flag Low	—	17	—	20	—	25	—	30	—	35	ns
tRFH	Read High to Full Flag High	—	20	—	23	—	25	—	30	—	35	ns
tWEF	Write High to Empty Flag High	—	20	—	23	—	25	—	30	—	35	ns
tWFF	Write Low to Full Flag Low	—	17	—	20	—	25	—	30	—	35	ns

NOTES:

1. Pulse widths less than minimum value are not allowed.
2. This parameter is guaranteed by design but not tested.
3. Preliminary specifications only.

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AC ELECTRICAL CHARACTERISTICS

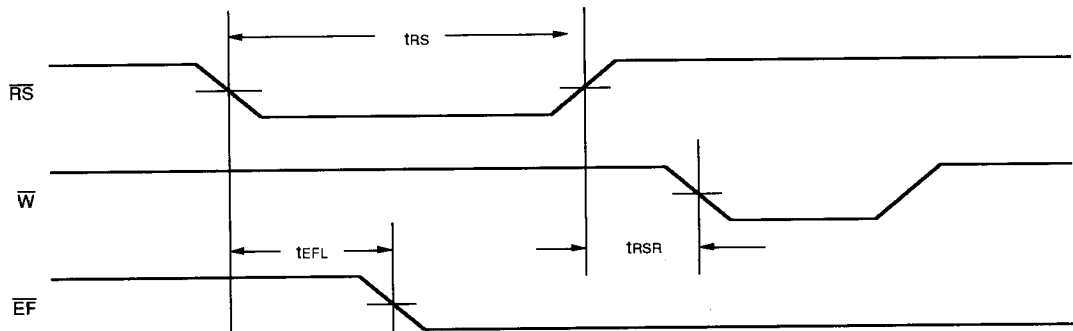
(Vcc = 5.0V ± 10%, TA = 0°C to +70°C)

Symbol	Parameter	7MP2009SxxZ, 7MP2010SxxZ								Unit
		-40		-50		-60		-70		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
tRC	Read Cycle Time	50	—	65	—	75	—	85	—	ns
tA	Access Time	—	40	—	50	—	60	—	70	ns
tRR	Read Recovery Time	10	—	15	—	15	—	15	—	ns
tRPW ⁽¹⁾	Read Pulse Width	40	—	50	—	60	—	70	—	ns
tRLZ ⁽²⁾	Read Pulse Low to Data Bus at Low Z	5	—	10	—	10	—	10	—	ns
tWLZ ⁽²⁾	Write Pulse High to Data Bus at Low Z	10	—	15	—	15	—	15	—	ns
tDV	Data Valid from Read Pulse High	5	—	5	—	5	—	5	—	ns
tRHZ ⁽²⁾	Read Pulse High to Data Bus at High Z	—	25	—	30	—	30	—	30	ns
tWC	Write Cycle Time	50	—	65	—	75	—	85	—	ns
tWPW ⁽¹⁾	Write Pulse Width	40	—	50	—	60	—	70	—	ns
tWR	Write Recovery Time	10	—	15	—	15	—	15	—	ns
tDS	Data Set-up Time	20	—	30	—	30	—	30	—	ns
tDH	Data Hold Time	0	—	5	—	5	—	10	—	ns
tRSC	Reset Cycle Time	50	—	65	—	75	—	85	—	ns
tRS ⁽¹⁾	Reset Pulse Width	40	—	50	—	60	—	70	—	ns
tRSR	Reset Recovery Time	10	—	15	—	15	—	15	—	ns
tEFL	Reset to Empty Flag Low	—	50	—	65	—	75	—	85	ns
tREF	Read Low to Empty Flag Low	—	40	—	50	—	60	—	70	ns
tRFF	Read High to Full Flag High	—	40	—	50	—	60	—	70	ns
tWEF	Write High to Empty Flag High	—	40	—	50	—	60	—	70	ns
tWFF	Write Low to Full Flag Low	—	40	—	50	—	60	—	70	ns

- NOTES:
- Pulse widths less than minimum value are not allowed.
 - This parameter is guaranteed by design but not tested.

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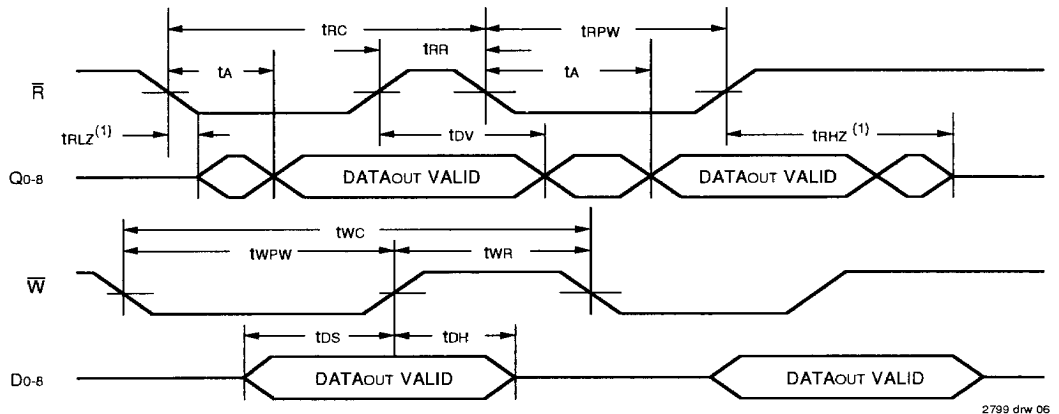
TIMING WAVEFORM OF RESET CYCLE^(1,2)



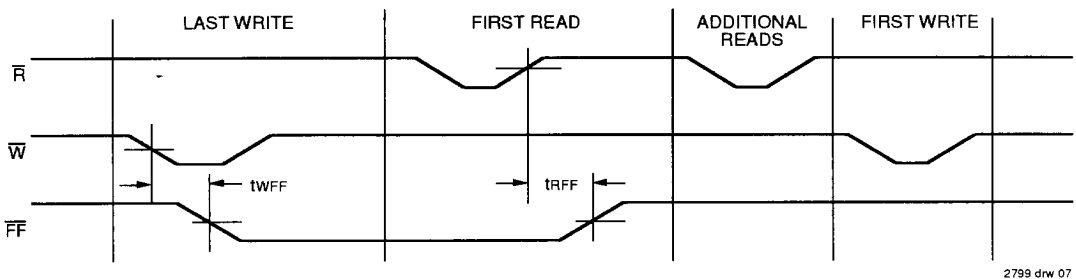
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- NOTES:
- tRSC = tRS + tRSR
 - W and R = VIH during RESET.

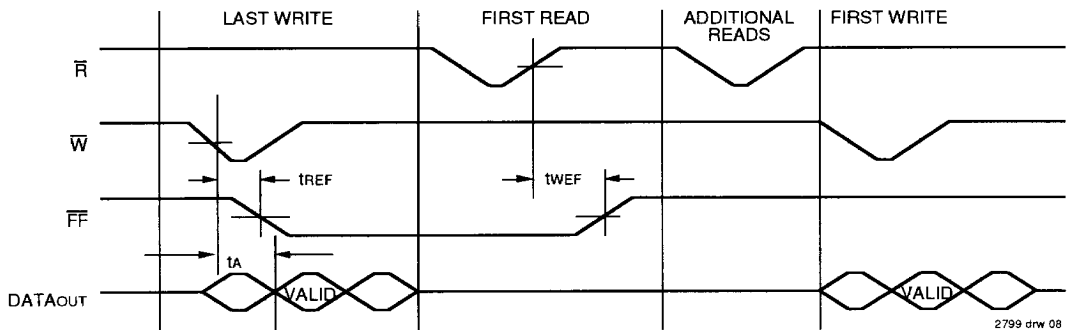
TIMING WAVEFORM OF ASYNCHRONOUS WRITE AND READ OPERATION



TIMING WAVEFORM FOR THE FULL FLAG FROM LAST WRITE TO FIRST READ



TIMING WAVEFORM FOR THE EMPTY FLAG FROM LAST READ TO FIRST WRITE⁽¹⁾

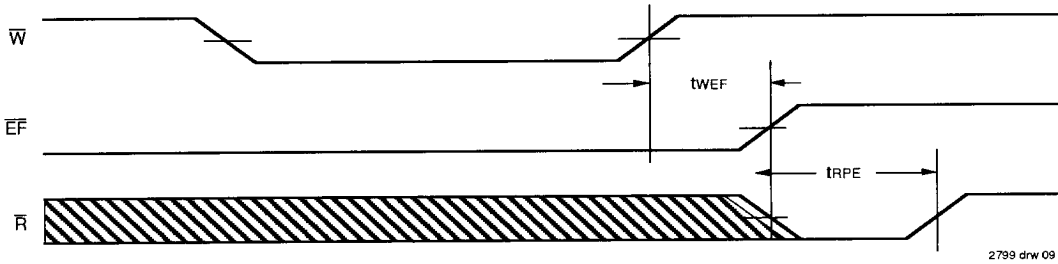


NOTE:

1. This parameter is guaranteed by design but not tested.

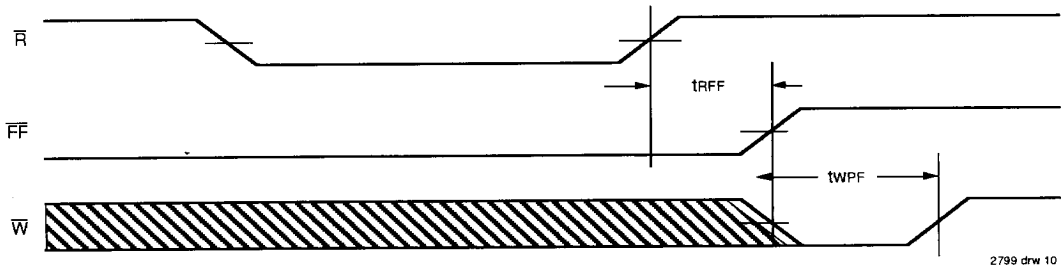
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TIMING WAVEFORM OF THE EMPTY FLAG CYCLE⁽¹⁾



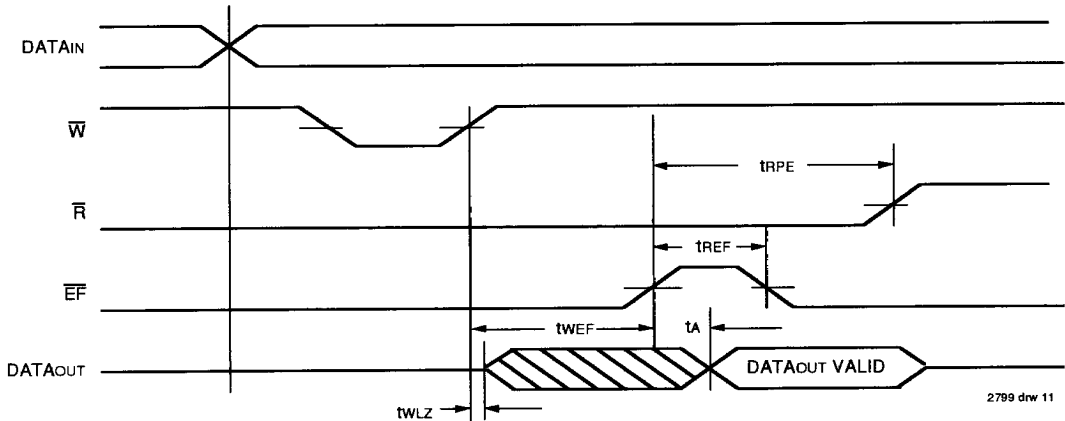
NOTE:
1. ($t_{RPE} = t_{RPW}$)

TIMING WAVEFORM OF THE FULL FLAG CYCLE

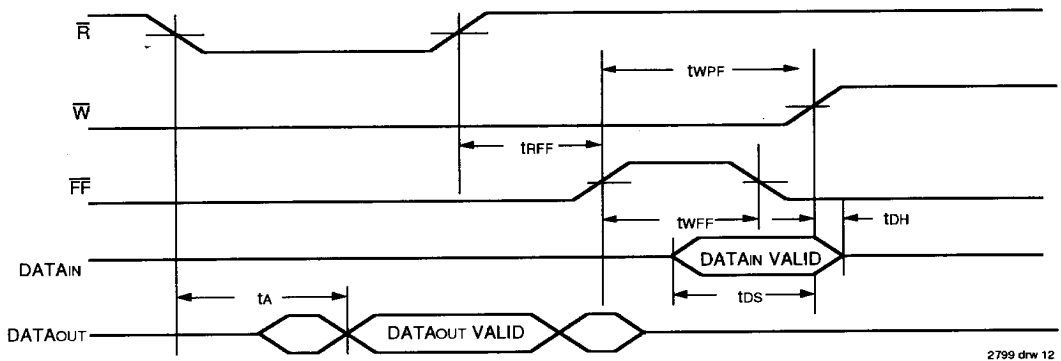


NOTE:
1. ($t_{WPF} = t_{WPW}$)

TIMING WAVEFORM OF READ DATA FLOW-THROUGH MODE



TIMING WAVEFORM OF WRITE DATA FLOW-THROUGH MODE

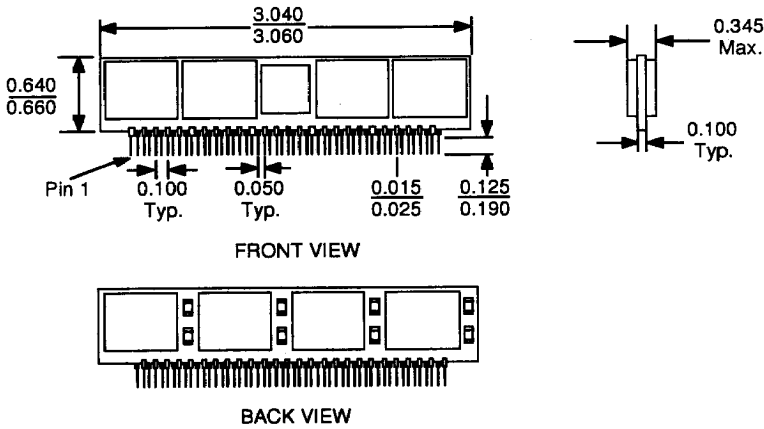


DEPTH/WIDTH EXPANSION & DATA FLOW-THROUGH MODES:

For more details on expanding FIFO modules in depth and/or width, please refer to the IDT7204 or IDT7205 data sheets.

For more details on data flow-through modes (read data fall-through and write data fall-through), please refer to the IDT7204 or IDT7205 data sheets.

PACKAGE DIMENSIONS



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